

Supplementary

Anharmonic atomic dynamics and thermal transport in SnTe with stoichiometric defects

Mayanak K Gupta^{1,2*}, Samiran Malgope^{1,2}, Sourav Bag¹, Ranjan Mittal^{1,2#}, Ajay Singh^{2,3}, and
Samrath L Chaplot^{1,2}

¹*Solid State Physics Division, Bhabha Atomic Research Centre, Trombay, Mumbai 400085, India*

²*Homi Bhabha National Institute, Anushaktinagar, Mumbai 400094, India*

³*Technical Physics Division, Bhabha Atomic Research Centre, Trombay, Mumbai 400085, India*

E-mail: *mayankg@barc.gov.in, #rmittal@barc.gov.in

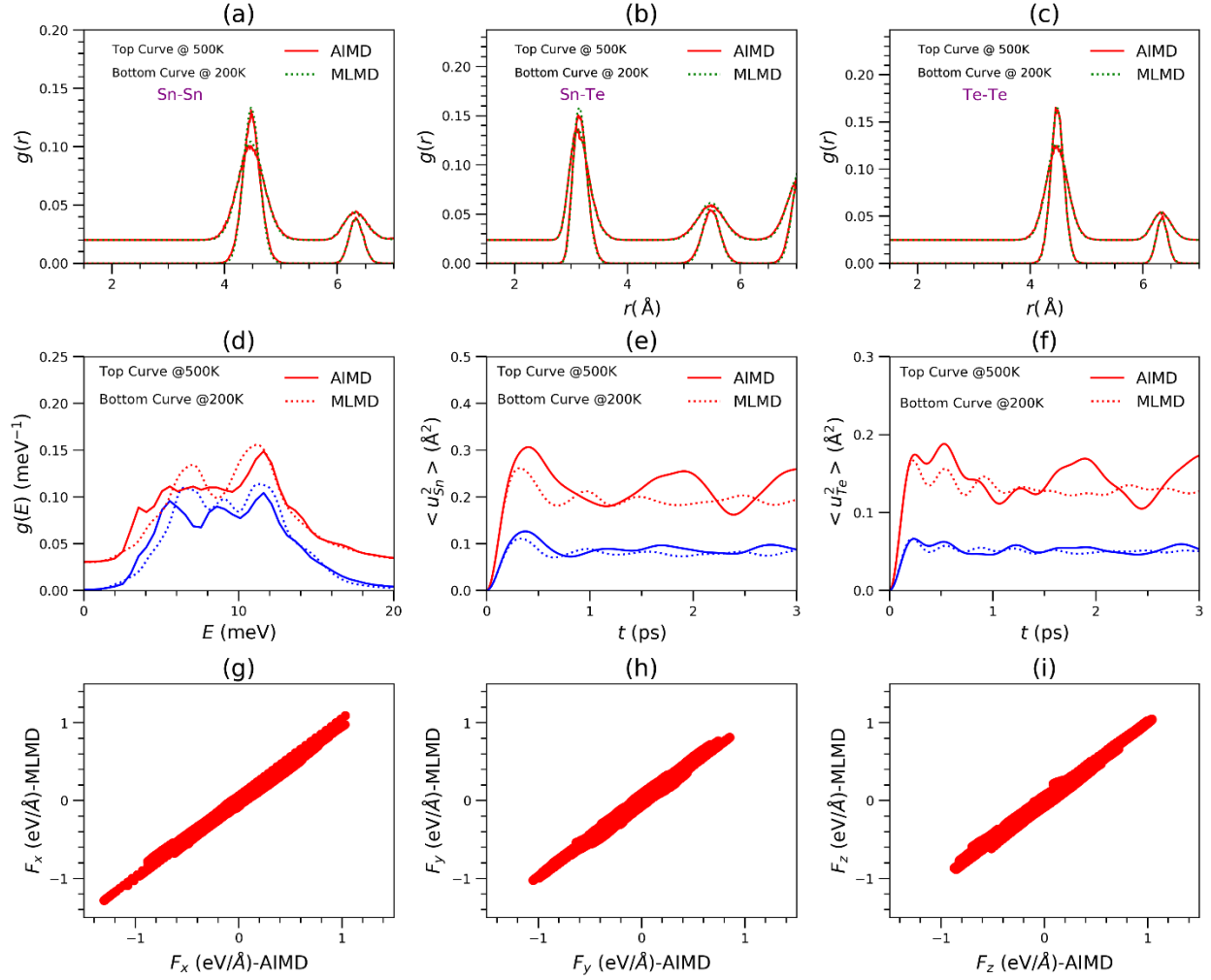


Figure S1. The benchmarking of Machine Learned Force Field by comparing the calculated (a-c) PDF, (d) PDOS and (e-f) MSD of SnTe using AIMD (solid line) and MLMD (dash line) at 200 K and 500 K, showing good overall agreement between the AIMD and MLMD results. (g-i) The computed forces from AIMD vs MLMD force-field on various configurations validate the model.

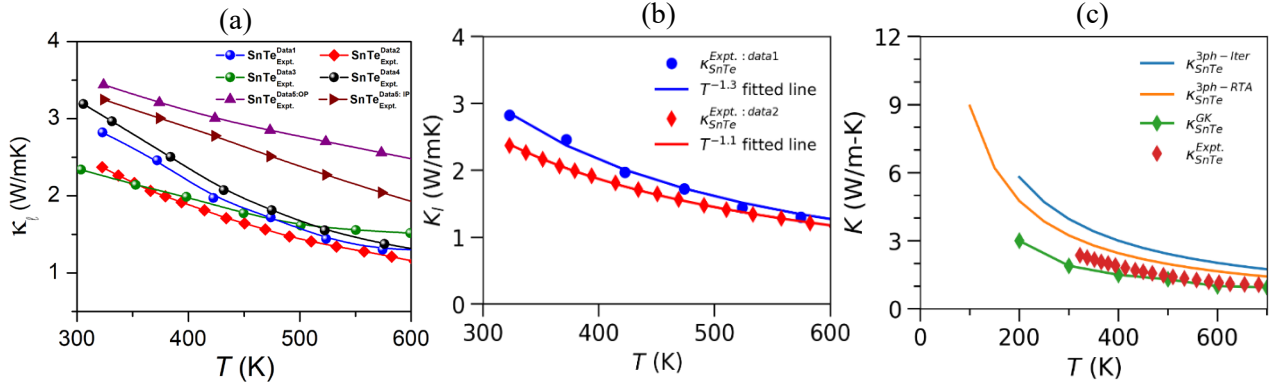


Figure S2.: (a) The measured lattice thermal conductivity of SnTe, reported in literatures¹⁻⁵, shows a significant variation in measured lattice thermal conductivity. (b) The temperature dependence of measured lattice thermal conductivity of SnTe^{1,2} show deviation from $1/T$ infers the presence of higher-order anharmonicity. (c) Our calculated lattice thermal conductivity of SnTe using different theoretical methods and compared with measured lattice thermal conductivity².

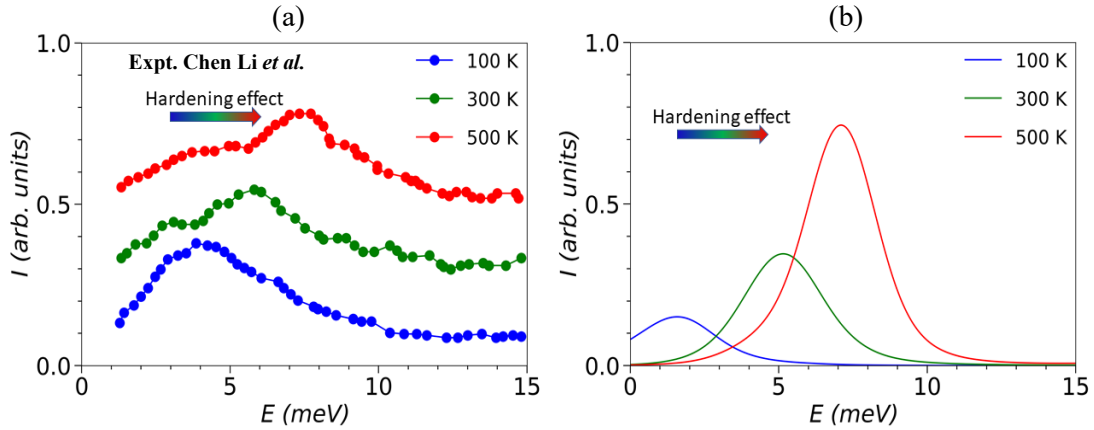


Figure S3: (a) The measured temperature dependence of the lowest zone-center optical phonon mode by Chen Li et al. shows the phonon hardening with temperature⁶, inferring the presence of 4th and higher-order phonon scattering. (b) Our calculated temperature dependence of the lowest zone-center optical phonon mode using molecular dynamics trajectories reproduces the hardening of phonon. This confirms that our simulations correctly capture the actual anharmonic effects, including higher-order anharmonicity, and validate the model's robustness.

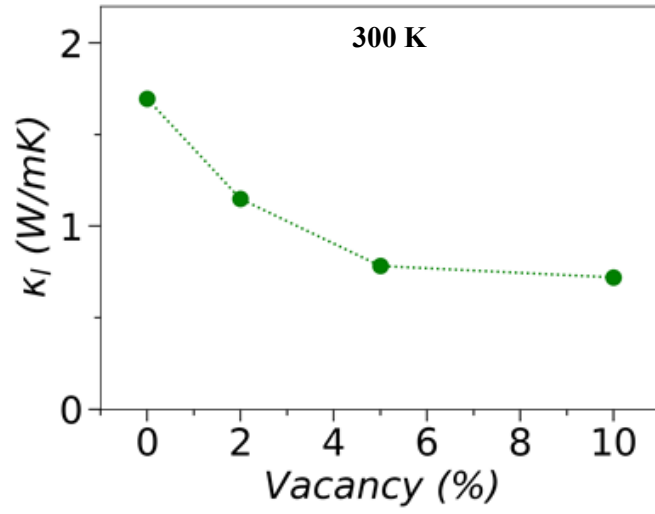


Figure S4: The calculated lattice thermal conductivity with different Sn vacancy concentrations at 300K using the Green-Kubo method. The Sn vacancy concentration plays a significant role in lowering the lattice thermal conductivity.

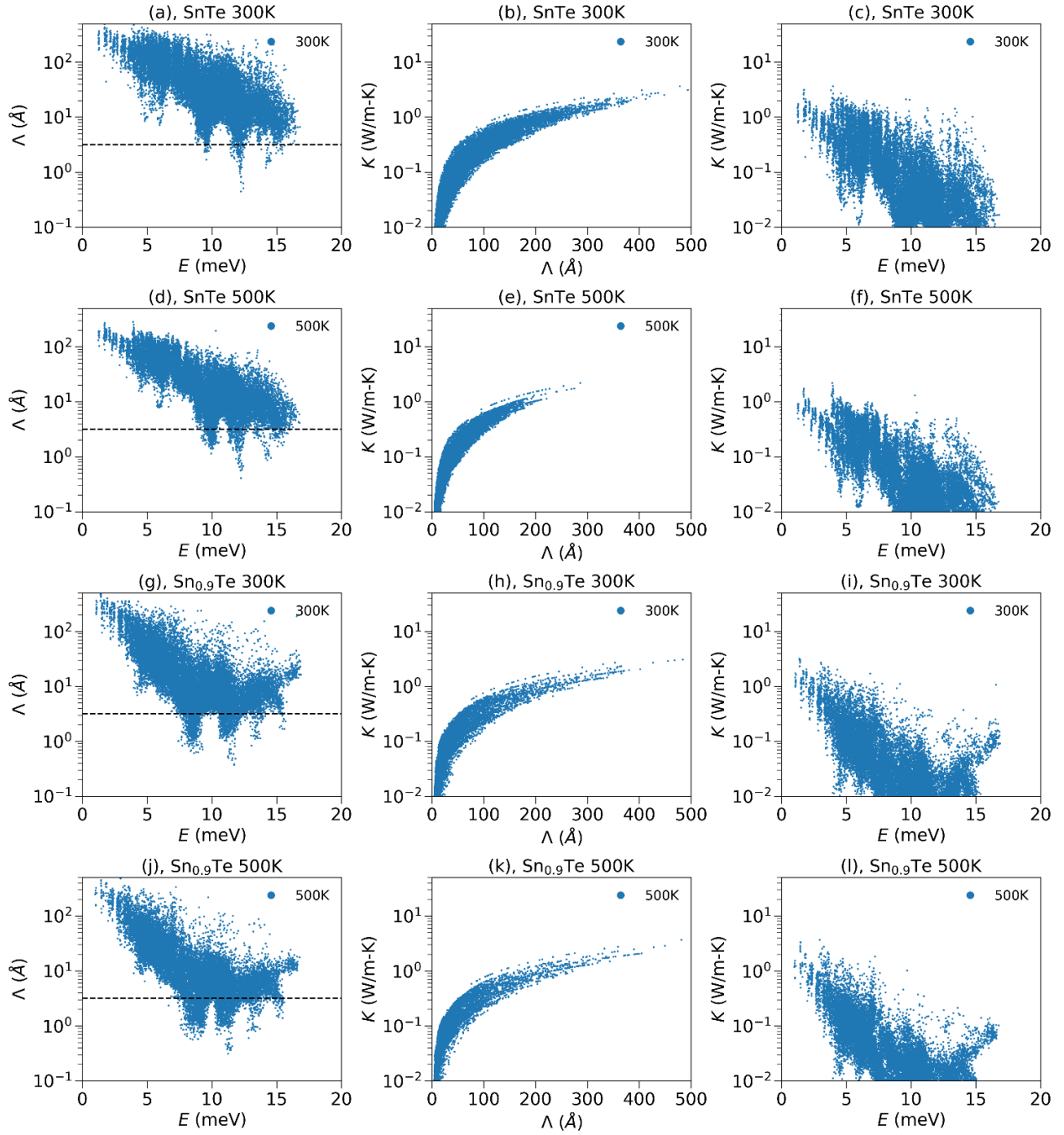


Figure S5: The calculated phonon mean free path (Λ), lattice thermal conductivity (κ) as a function of phonon mean free path, and phonon energies in the entire Brillouin zone using molecular dynamics trajectories at 300 K and 500 K for both (a-f) SnTe and (g-l) $\text{Sn}_{0.9}\text{Te}$.

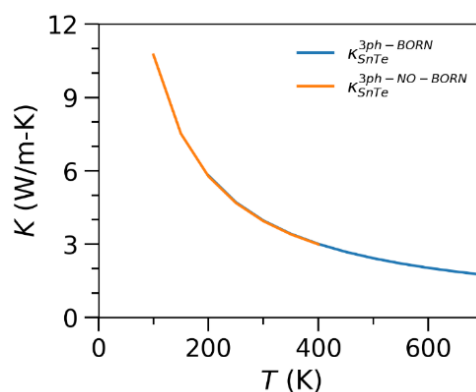


Figure S6: The calculated lattice thermal conductivity with and without including the Born effective charges. The Born-effective charges do not influence the lattice thermal conductivity.

1. J.-W. Zhang, Z.-W. Wu, B. Xiang, N.-N. Zhou, J.-L. Shi and J.-X. Zhang, *ACS applied materials & interfaces*, 2020, **12**, 21863-21870.
2. X. Xu, J. Cui, Y. Huang, J. Xia, K. Pan, L. Xie and J. He, *ACS Applied Materials & Interfaces*, 2023, **15**, 9656-9664.
3. S.-X. Lin, X. Tan, H. Shao, J. Xu, Q. Wu, G.-Q. Liu, W.-H. Zhang and J. Jiang, *The Journal of Physical Chemistry C*, 2019, **123**, 15996-16002.
4. Y.-X. Chen, F. Li, D. Li, Z. Zheng, J. Luo and P. Fan, *Materials*, 2019, **12**, 3001.
5. S. P. Keshri and A. Medhi, *Journal of Physics: Condensed Matter*, 2020, **33**, 115701.
6. C. W. Li, O. Hellman, J. Ma, A. F. May, H. B. Cao, X. Chen, A. D. Christianson, G. Ehlers, D. J. Singh, B. C. Sales and O. Delaire, *Physical Review Letters*, 2014, **112**, 175501.